

ECSS-Q-HB-60-02

HANDBOOK

“Techniques for Radiation Effects Mitigation in ASICs and FPGAs”

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Microelectronics Section
ESA / ESTEC

- **Scope and goals of Handbook**
- **When and who prepared this Handbook?**
- **Classification of mitigation techniques, structure of HB**
- **Overview of main chapters (lists of techniques)**

Deciphering the handbook coded name



**Space product
assurance
(branch “Q”)**

ECSS-Q-HB-60-02

Handbook

**EEE
Components
(discipline “60”)**

**“Techniques for
Radiation Effects
Mitigation in
ASICs and
FPGAs”**

compilation of

techniques to mitigate effects of radiation in ASICs & FPGAs
techniques **grouped** according to the different stages (levels) of an IC development flow

in addition

- overview of the space radiation environment and its effects in ICs
- general guidelines for selecting techniques , how to use the handbook
- how to validate the mitigation techniques

intended users

Engineers and IC designers doing selection, use or development of
ASIC or FPGA to be used in radiation environment

Intended use

As guidelines and references only, not requirements

History of ECSS-Q-**HB**-60-02



2006 2007 2008 2009 2010 2011 2012 2013 2014 2015 2016

-
- 2007/07:** ECSS-Q-**ST**-60-02: “**ASIC and FPGA development**” **standard** released
- 2010/03:** contract KO to develop 1st ECSS-Q-**HB**-60-02 draft: “**Techniques for Radiation Effects Mitigation in ASICs and FPGAs**” by **TIMA(F)** et al.
- 2010/09:** workshop on the topic at ESA/ESTEC
- 2011/12:** Final presentation (version 6 of the HB 1st draft) with training at ESTEC
- 2012/02:** Final revision to the HB (version 7), with inputs from TIMA & ESTEC
- 2013/10:** “**ECSS Working Group**” KO to improve the 1st HB draft for future ECSS public review
- 2014-today:** ECSS Working Group and Secretariat preparing improved HB draft

Who worked in the ECSS-Q-HB-60-02 ?



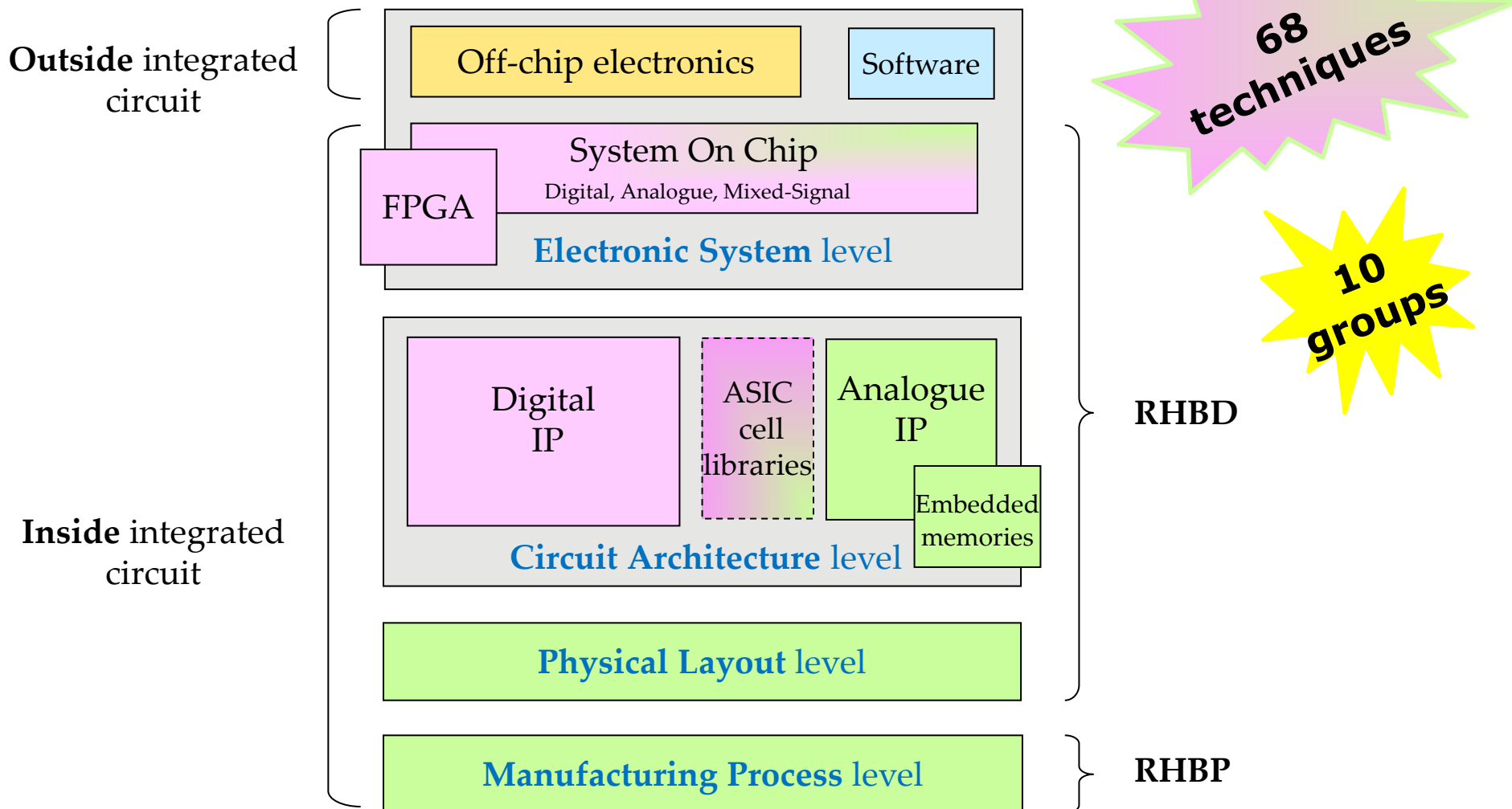
First HB draft (2012 Q1) put together by **TIMA (F)**, under **ESA** contract, with key inputs from:

M. Alles	University of Vanderbilt (USA)	process and layout level
D. Loveless		analogue & mixed-signal circuits
M. Nicolaidis	TIMA (F)	digital circuits
R. Velazco		HB contract manager
B. Glass	European Space Agency (NL)	
F. L. Kastensmidt	Universidade Federal do Rio Grande do Sul (Brazil)	Digital circuits and FPGAs
M. Violante	Politecnico di Torino (I)	Embedded Software
M. Pignol	CNES (F)	System architecture

Final HB version (2015 Q3) by the ECSS WG with inputs/corrections from **ESA, Thales, AirbusDS, RUAG, OHB, CNES(F), CERN(CH) and IMEC(B)** ...and **anyone interested** through “Public Review”

Over 350 citations of industry, academia, vendors and agencies worldwide

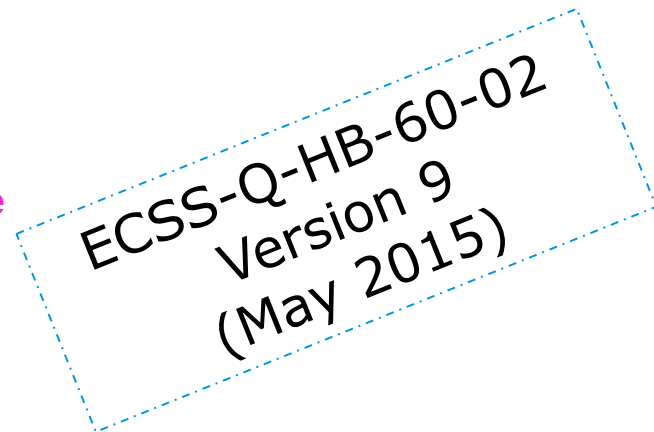
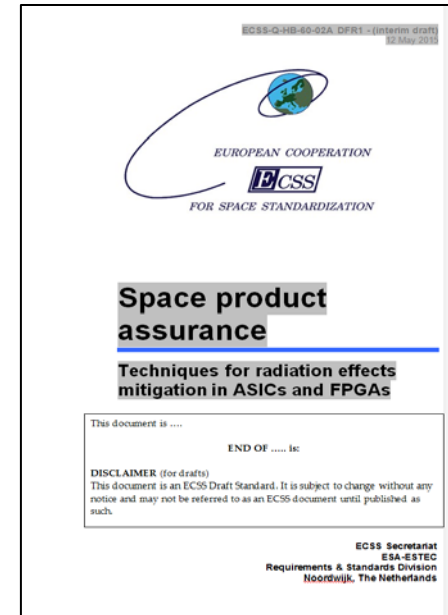
classification of mitigation techniques, abstraction levels



Handbook table of contents

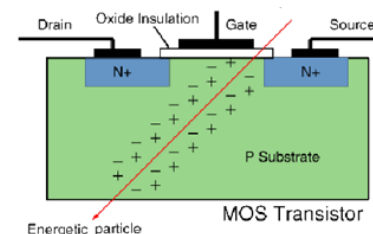
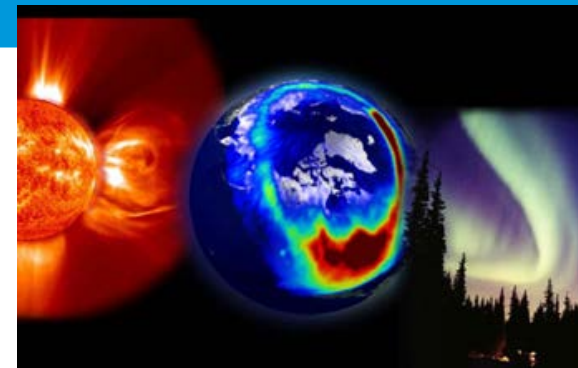


size (pages)	chapter #	chapter title
10	1	Scope
	2	References
	3	Terms, definitions and abbreviated terms
5	4	Radiation environment and integrated circuits
2	5	Choosing a design hardening strategy
15	6	Technology selection and process level mitigation
12	7	Layout
29	8	Analogue circuits
22	9	Embedded memories
6	10	Radiation-hardened ASIC libraries
20	11	Digital Circuits
18	12	System on a Chip
26	13	Field Programmable Gate Arrays
15	14	Software-implemented hardware fault tolerance
17	15	System architecture
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3	Annex B	Vendor Solutions

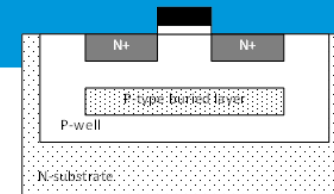


- a. Overview
- b. Table of Mit. Techniques vs. Rad Effects
- c. Mitigation techniques descriptions, with examples, figures...
 - Available Test Data (simulations, radiation testing, in-flight)
 - Added value (efficiency)
 - Known issues (Weaknesses, elements to be considered)
 - “ID card”
 - Abstraction level
 - Pros
 - Cons
 - Mitigated effects
 - Validation Methods
 - Automation tools
 - Vendor solutions

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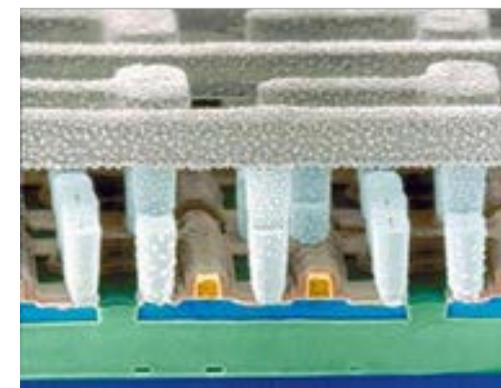
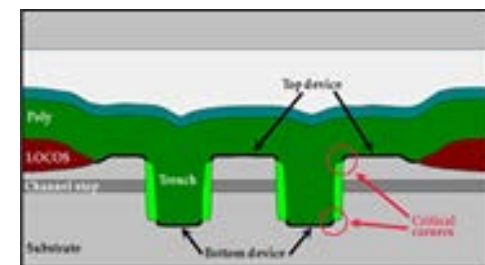


6 Technology selection and process level mitigation



6 Technology selection and process level mitigation

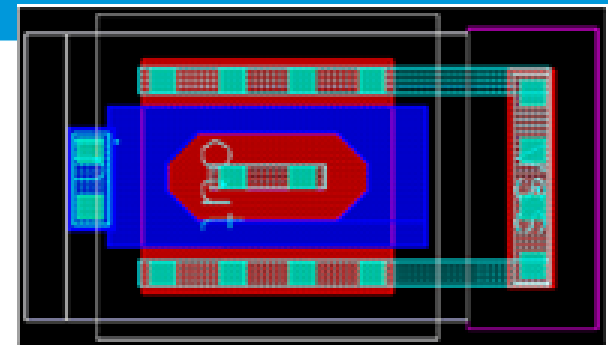
- 6.1 Overview
- 6.2 Summary of effects vs mitigation techniques
- 6.3 Mitigation techniques
 - 6.3.1 Epitaxial layers
 - 6.3.2 Silicon On Insulator
 - 6.3.3 Triple wells
 - 6.3.4 Buried layers
 - 6.3.5 Dry thermal oxidation
 - 6.3.6 Implantation into oxides
- 6.4 Technology scaling and radiation effects



7 Layout

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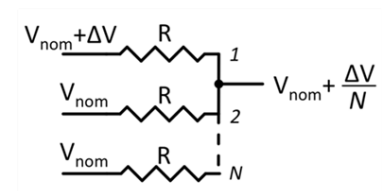
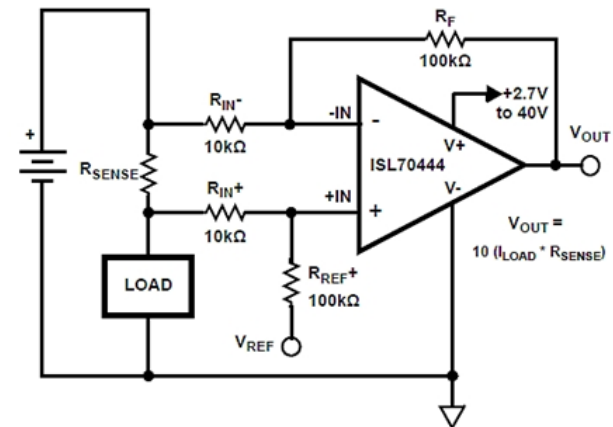
- 7.3.1 Ringed or Enclosed Layout Transistor
- 7.3.2 Contacts and guard rings
- 7.3.3 Dummy transistors
- 7.3.4 Large W/L ratio transistors



8 Analogue circuits

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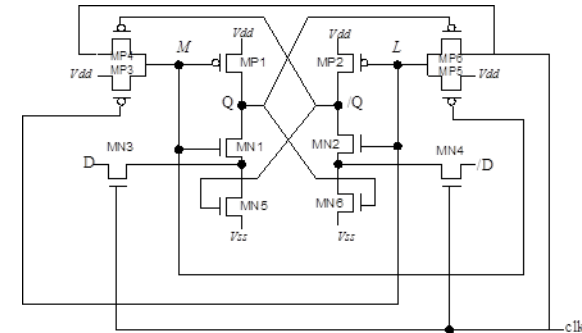
- 8.3.1 Node Separation and Inter-digitation
- 8.3.2 Analogue Redundancy (Averaging)
- 8.3.3 Resistive Decoupling
- 8.3.4 Filtering
- 8.3.5 Modifications in Bandwidth, Gain, Operating Speed, and Current Drive
- 8.3.6 Reduction of Window of Vulnerability
- 8.3.7 Reduction of High Impedance Nodes
- 8.3.8 Differential Design
- 8.3.9 Dual Path Hardening



9 Embedded memories

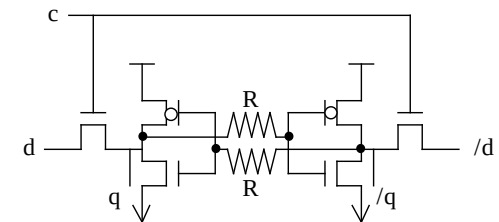
9.3.1 Hardening of individual Memory Cells

- 9.3.1.1 Resistive hardening
- 9.3.1.2 Capacitive hardening
- 9.3.1.3 IBM hardened memory cell
- 9.3.1.4 HIT hardened memory cell
- 9.3.1.5 DICE hardened memory cell
- 9.3.1.6 NASA-Whitaker hardened memory cell
- 9.3.1.7 NASA-Liu hardened memory cell



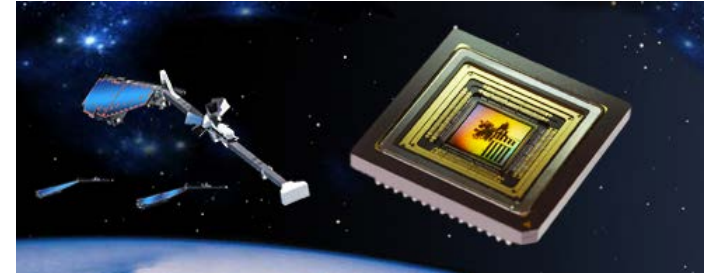
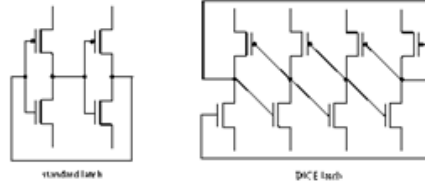
9.3.2 Bit-interleaving in memory arrays

9.3.3 Data Scrubbing



9.4 Comparison between hardened memory cells

10 Radiation-hardened ASIC libraries



- 10.1 IMEC Design Against Radiation Effects (DARE) 0.18 μm library
- 10.2 CERN 0.25 μm , 65nm rad hard library
- 10.3 BAE 0.15 μm rad hard library
- 10.4 Ramon Chips 0.18 μm and 0.13 μm rad hard libraries
- 10.5 Aeroflex 600, 250, 130 and 90 nm rad hard libraries
- 10.6 Atmel MH1RT, ATC18RHA, ATMX150RHA (0.35, 0.18 & 0.15 μm) rad hard lib
- 10.7 ATK 0.35 μm rad hard cell library
- 10.8 ST Microelectronics C65SPACE 65nm rad hard library
- 10.9 RedCat Devices 0.18 μm and 0.13 μm rad hard libraries

11 Digital Circuits

...

11.3.1 Spatial redundancy

11.3.1.1 Duplex architectures

11.3.1.2 Triple Modular Redundancy architectures

11.3.1.2.1 Basic TMR

11.3.1.2.2 Full TMR

11.3.2 Temporal redundancy

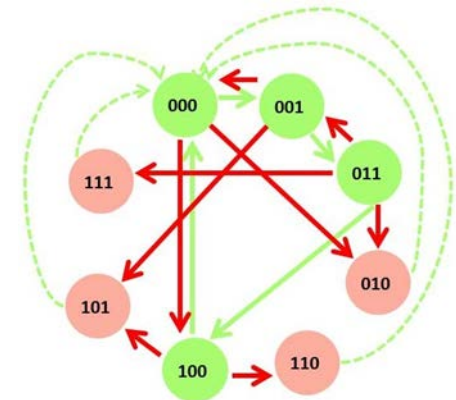
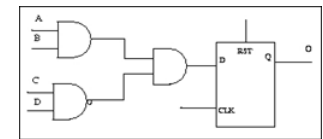
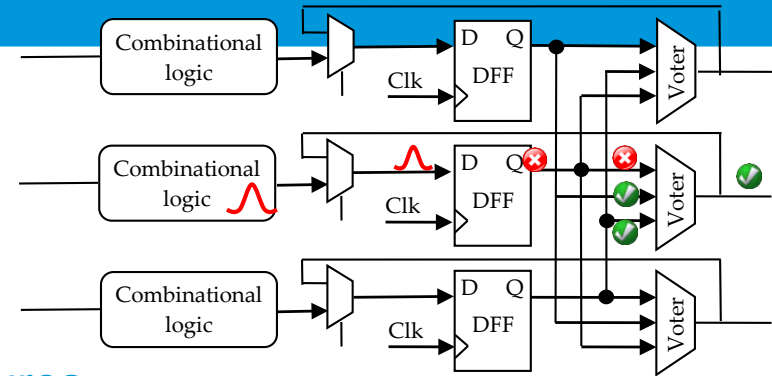
11.3.2.1 Triple Temporal Redundancy combined with spatial redundancy

11.3.2.2 Minimal level sensitive latch

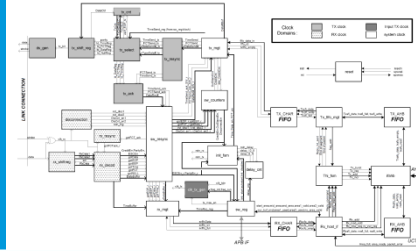
11.3.3 Fail-Safe, Deadlock-free Finite State Machines

11.3.4 Selective use of logic cells

b)



12 System on a Chip



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12.3.1 Error Correcting Codes

12.3.1.1 Parity check

12.3.1.2 Cyclic Redundancy Check

12.3.1.3 BCH codes

12.3.1.4 Hamming codes

12.3.1.5 SEC-DED codes

12.3.1.6 Reed-Solomon codes

12.3.1.7 Arithmetic codes

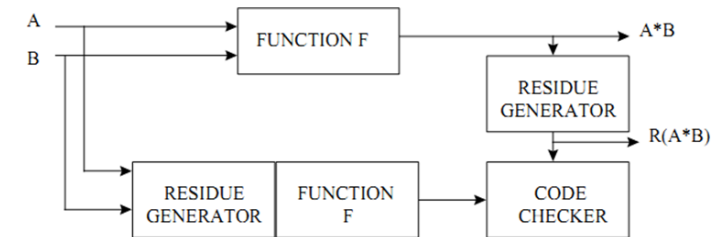
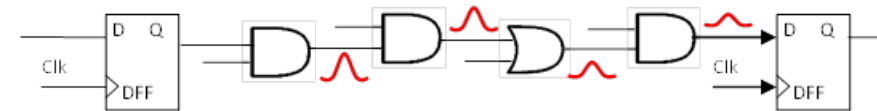
12.3.1.8 Low Density Parity Codes

12.3.2 Mitigation for Memory Blocks

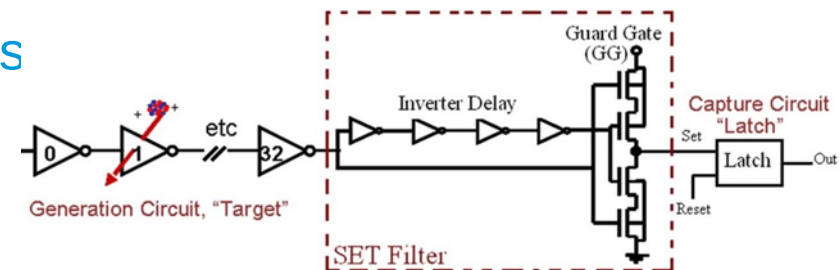
12.3.3 Filtering SET pulses in data paths

12.3.4 Watchdog timers

12.3.5 TMR in mixed-signal circuits

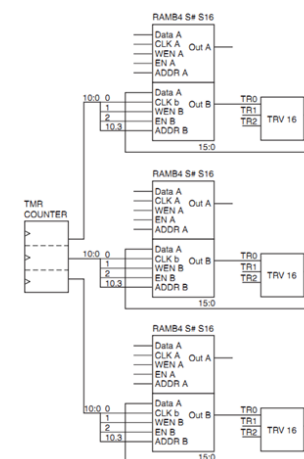
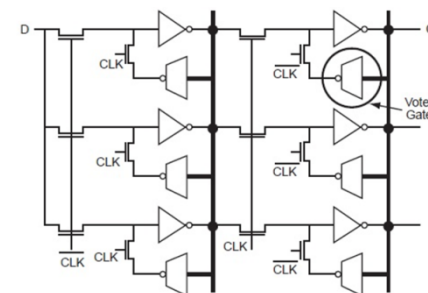
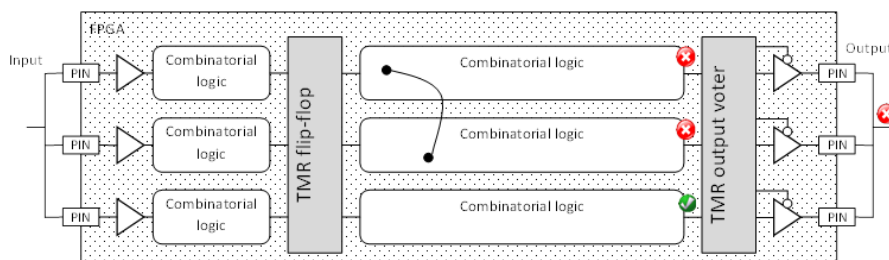


7 bits of data	Number of "1"	8-bits including parity bit	
		even	odd
000 0000	0	<u>0</u> 000 0000	<u>1</u> 000 0000
101 0001	3	<u>1</u> 101 0001	<u>0</u> 101 0001
110 1001	4	<u>0</u> 110 1001	<u>1</u> 110 1001
111 1111	7	<u>1</u> 111 1111	<u>0</u> 111 1111



13 Field Programmable Gate Arrays

- 13.3.1 Local TMR
- 13.3.2 Global TMR
- 13.3.3 Large grain TMR
- 13.3.4 Embedded user memory TMR
- 13.3.5 Additional Voters in TMR data-paths to minimise DCE
- 13.3.6 Reliability-oriented place and Route Algorithm (RoRA)
- 13.3.7 Embedded processor protection
- 13.3.8 Scrubbing of configuration memory



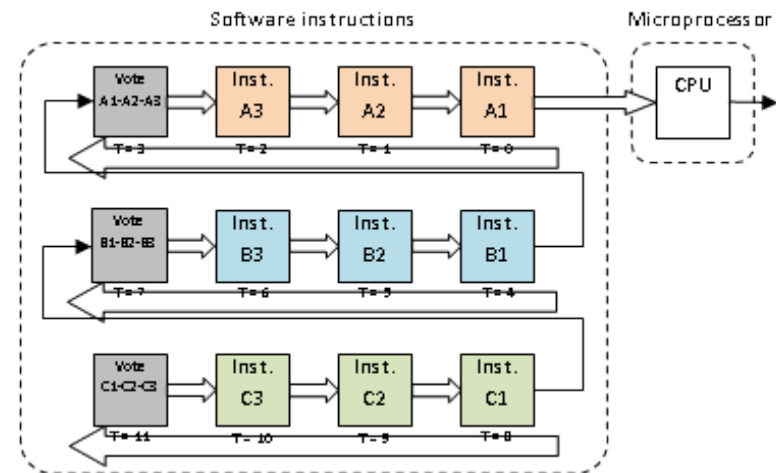
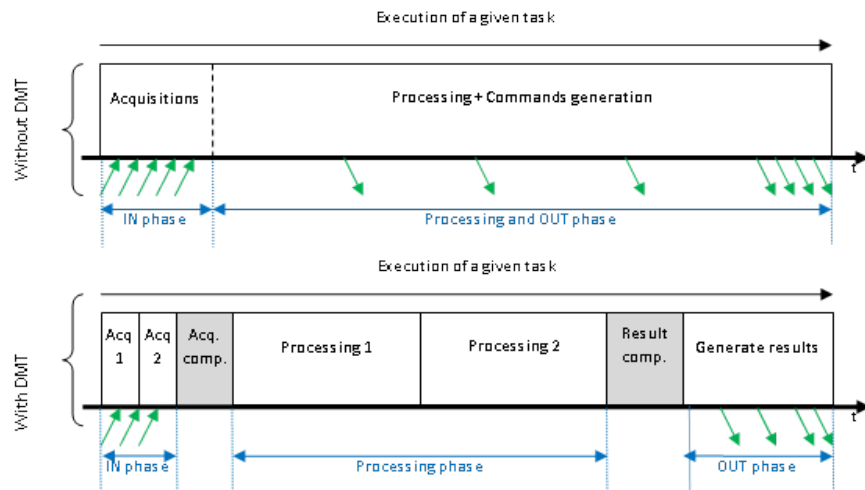
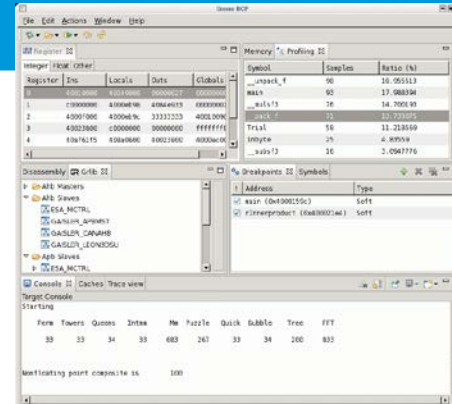
+ techniques in Chapters 11 (digital) & 12 (SoC)

14 Software-implemented hardware fault tolerance

14.3.1 Redundancy at **instruction** level

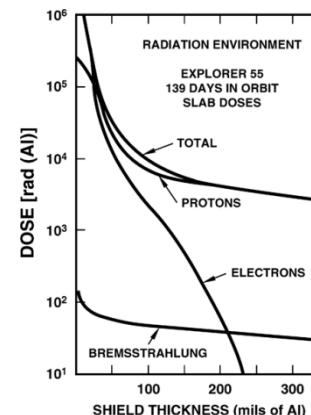
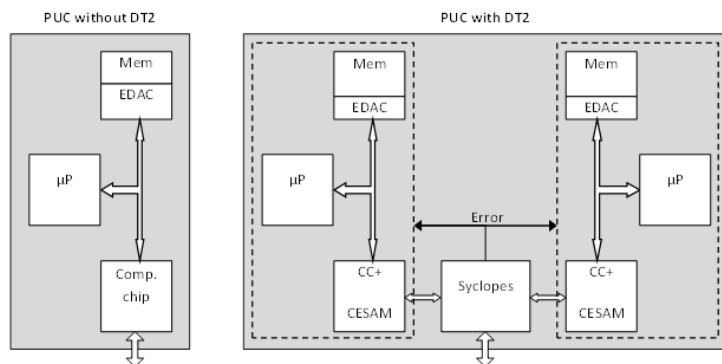
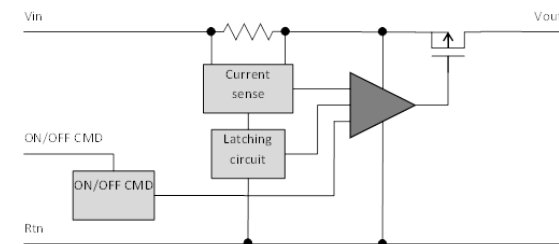
14.3.2 Redundancy at **task** level

14.3.3 Redundancy at **application** level: using a hypervisor



15 System architecture (off-chip)

- 15.3.1 Shielding
- 15.3.2 Watchdog timers
- 15.3.4 Latching current limiters
- 15.3.5 Spatial Redundancy
 - 15.3.5.1 Duplex architectures
 - 15.3.5.1.1 Lockstep
 - 15.3.5.1.2 Double Duplex
 - 15.3.5.1.3 Double Duplex Tolerant to Transients (DT2)
 - 15.3.5.2 Triple Modular Redundancy
- 15.3.6 Error Correcting Codes
- 15.3.7 Off-chip SET filters



Power cycling



TMR variants in this Handbook

	11 – Digital Circuits	12 - SoC	13 - FPGA	15 – Off-chip		3x flip flops	3x combinatorial logic	3x voter	Extra voters in data paths	Triplets physical layout separated	3x memory blocks	comparing analog signals	3x chip	Synchronizing logic	3x outputs
Basic TMR	x					x									
Full TMR	x					x	x	x							
Local TMR			x			x									
Global TMR			x			x	x	x							x
Large grain TMR			x			x	x	x		x					x
Embedded memory TMR			x								x				
TMR with voters against DCE			x			x	x	x	x						
Mixed-signal TMR		x										x			
Chip-level TMR				x									x	x	

16 Validation methods

16.2

Fault injection

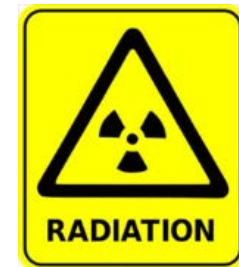
- 16.2.1 Fault injection at transistor level
 - 16.2.1.1 Physical level 2D/3D device simulation
 - 16.2.1.2 Transient fault injection simulations at electrical level
- 16.2.2 Fault injection at gate level
- 16.2.3 Fault injection at device level
 - 16.2.3.1 Fault injection in processors
 - 16.2.3.2 Fault injection in FPGAs
 - 16.2.3.3 Analytical methods for predicting effects of soft errors on SRAM-based FPGAs
- 16.2.4 Fault injection at system level



16.3

Real-life radiation tests

- 16.3.1 Tests on-board scientific satellites
- 16.3.2 On-board stratospheric balloons
- 16.3.3 Ground level tests



16.4

Ground accelerated radiation tests

- 16.4.1 Standards and specifications
- 16.4.2 SEE test methodology
 - 16.4.2.1 Static test
 - 16.4.2.2 Dynamic test
- 16.4.3 TID test methodology
- 16.4.4 TID and SEE test facilities
 - 16.4.4.1 Total ionizing dose
 - 16.4.4.2 Single event effects
- 16.4.5 Complementary SEE test strategies
 - 16.4.5.1 **Laser beams** SEE tests
 - 16.4.5.2 **Ion-Microbeam** SEE tests
 - 16.4.5.3 **Californium-252 and Americium-241** SEE tests
- 16.4.6 SEE tests practical constraints and DUT preparation



2015/06: ECSS-Q-HB-60-02 release for ECSS “**public review**”
(2 months approx)

= => please check here: <http://www.ecss.nl/>
to download Handbook during public review
and form to submit **your feedback** !

2015/Q3: ECSS-Q-HB-60-02 **final release** as an official new ECSS
Handbook



THANKS!

Questions? Suggestions?

ECSS-Q-HB-60-02 Handbook

“Techniques for Radiation Effects Mitigation in ASICs and FPGAs”

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